



2019년 2월 14일(목), 11:00-12:30

Room C (가람홀, 2층)

[TC2-F] Nanowire FETs

좌장: 김경록 교수(UNIST), 최우영 교수(서강대학교)

<p>TC2-F-1 11:00-11:15</p>	<p>Design and Fabrication of Multi-Channel Nanowire SiGe MOSFET Eunseon Yu¹, Jae Hwa Seo², Baegmo Son³, Sangjoon Park³, Won-Jun Lee⁴, Jongwan Jung⁴, and Seongjae Cho¹ <i>¹Department of Electronics Engineering, Gachon University, ²Department of Electrical and Computer Engineering, Seoul National University, ³Wonik IPS, ⁴Department of Nanotechnology and Advanced Materials Engineering, Sejong University</i></p>
<p>TC2-F-2 11:15-11:30</p>	<p>Simulation Study on the Effect of Parasitic Channel Height on Characteristics of Stacked Gate-All-Around Nanosheet FET Yunho Choi¹, Kitae Lee¹, Kyoung Yeon Kim, Sihyun Kim¹, Junil Lee¹, Ryoongbin Lee¹, Hyun-Min Kim¹, Young Suh Song¹, Sangwan Kim², and Byung-Gook Park¹ <i>¹Department of Electrical and Computer Engineering, Seoul National University, ²Department of Electrical and Computer Engineering., Ajou University</i></p>
<p>TC2-F-3 11:30-11:45</p>	<p>Effect of Process-Induced Line Edge Roughness on Performance of Gate-All-Around FET Jinhong Min and Changhwan Shin <i>Department of Electrical and Computer Engineering, Sungkyunkwan University</i></p>
<p>TC2-F-4 11:45-12:00</p>	<p>Comparison of Self-Heating Effects in 3.5nm Node Nanoplate-FET Using Corner Spacer Hyunwoo Kim¹, Hyunsuk Kim¹, Myounggon Kang², Jongwook Jeon³, and Hyungcheol Shin¹ <i>¹Department of Electrical and Computer Engineering, Seoul National University, ²Department of Electronics Engineering, Korea National University of Transportation, ³Department of Electronics Engineering, Konkuk University</i></p>
<p>TC2-F-5 12:00-12:15</p>	<p>Investigation of Omega-Shaped-Gate Nanowire FETs Young Suh Song^{1,2}, Taehyung Kim^{1,2}, Kyung Kyu Min^{1,2}, Sungmin Hwang^{1,2}, Yunho Choi^{1,2}, and Byung-Gook Park^{1,2} <i>¹Department of Electrical and Computer Engineering, Seoul National University, ²Inter-University Semiconductor Research Center, Seoul National University</i></p>
<p>TC2-F-6 12:15-12:30</p>	<p>Characteristics of Band Modulation FET 권세현¹, 최민호⁴, 박인성^{1,2}, 김용태⁴, 안진호^{1,2,3} <i>¹한양대학교 신소재공학과, ²한양대학교 나노반도체공학과, ³한양대학교 나노과학기술연구소, ⁴한국과학기술연구원</i></p>